8550SS

TO-92 Plastic-Encapsulate Transistors

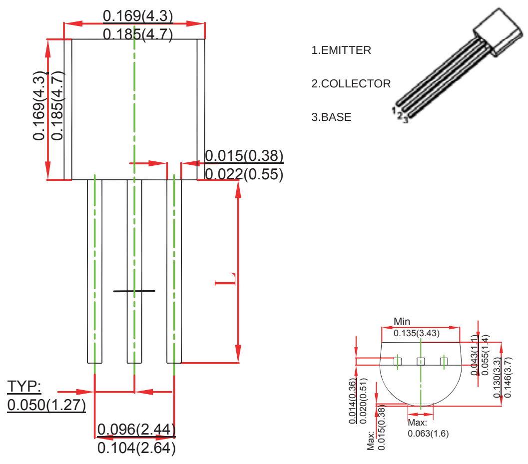
FEATURES

- General Purpose Switching and Amplification.
- TRANSISTOR (PNP)

MECHANICAL DATA

- Case style:TO-92 molded plastic
- Mounting position:any

TO-92



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-1.5	A
P_C	Collector Power Dissipation	1	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	125	℃ /W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃

ELECTRICAL CHARACTERISTICS T_a=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= -0.1mA,I_E=0	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-0.1mA,I_B=0	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-0.1mA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-40V,I_E=0			-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}=-20V,I_B=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V,I_C=0			-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-1, I_C=-100mA	85		300	
	$h_{FE(2)}$	V_{CE}=-1V, I_C=-800mA	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-800mA,I_B=-80mA			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-800mA,I_B=-80mA			-1.2	V
Transition frequency	f_T	V_{CE}=-10V,I_C=-50mA,f=30MHz	100			MHz

CLASSIFICATION OF $h_{FE(1)}$

RANK	**B**	**C**	**D**
RANGE	85-160	120-200	160-300

RATINGS AND CHARACTERISTIC CURVES

Typical Characterisitics